

Silicon NPN Power Transistors

2SD1290

DESCRIPTION

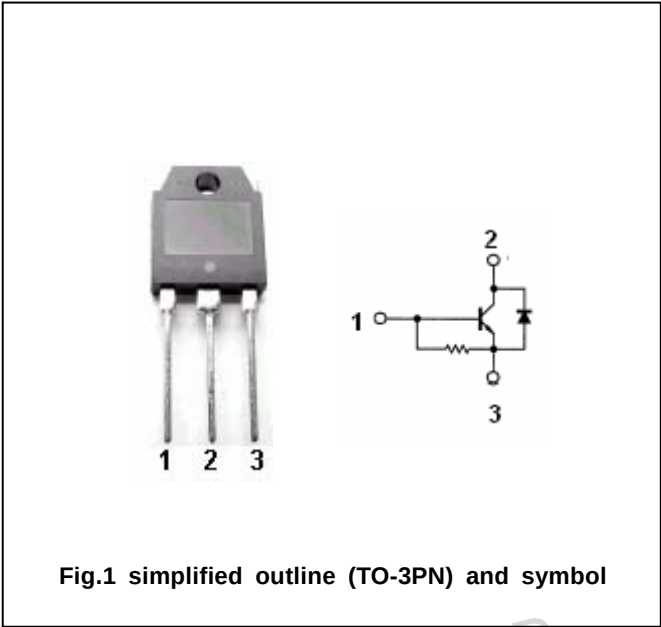
- With TO-3PN package
- Built-in damper diode
- High voltage ,high reliability
- Wide area of safe operation

APPLICATIONS

- For color TV horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current (DC)		3	A
I_{CM}	Collector current (Pulse)		10	A
P_C	Collector power dissipation	$T_C=25^{\circ}C$	50	W
T_j	Junction temperature		130	$^{\circ}C$
T_{stg}	Storage temperature		-55~130	$^{\circ}C$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=500mA; I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=2A; I_B=0.75A$			5.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=2A; I_B=0.75A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=750V; I_E=0$			50	μA
		$V_{CB}=1500V; I_E=0$			1	mA
h_{FE}	DC current gain	$I_C=2A; V_{CE}=10V$	3		8	
t_s	Storage time	$I_C=2A$ $I_{Leak}=0.75A, L_B=5 \mu H$	3		7	μs
t_f	Fall time				1	μs
V_F	Diode forward voltage	$I_F=-4A, I_B=0$			2.2	V

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PACKAGE OUTLINE

